

#### **Description**

The AO3406 uses advanced trench technology

to provide excellent  $R_{\text{DS}(\text{ON})},$  low gate charge and

operation with gate voltages as low as 4.5V. This

device is suitable for use as a

Battery protection or in other Switching application.



#### **General Features**

 $V_{DS} = 30V I_{D} = 5.8A$ 

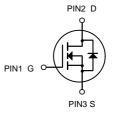
 $R_{DS(ON)}$  < 28m $\Omega$ @ V<sub>GS</sub>=10V

### **Application**

Battery protection

Load switch

Uninterruptible power supply



N-Channel MOSFET

### **Package Marking and Ordering Information**

Product ID	Pack	Brand	Qty(PCS)
AO3406	SOT-23-3L	HXY MOSFET	3000

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

symbol	parameter		unit
V <sub>DS</sub>	Drain-source voltage		V
V <sub>G</sub> S	Gate-source voltage		V
ID	Drain current-continuous³@Tj=125℃		А
IDM	-pulse <i>d</i> <sup>b</sup>	20	А
Is	Drain-source Diode forward current		А
P <sub>D</sub>	Maximum power dissipation		W
Tj	Operating junction Temperature range		°C
Rth JA	Thermal Resistance junction-to ambient	100	°C/W



# **Electrical Characteristics** (TA=25°C unless otherwise noted)

Symbol	Condition	Min	Тур	Max	Unit
BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250μA	30	-	-	V
IDSS	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	μA
IGSS	V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V	-	-	±100	nA
VGS(th)	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA	0.8	1.4	2.2	V
	V <sub>GS</sub> =10V, I <sub>D</sub> =5A	-	24	28	
RDS(ON)	V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A		26	32	mΩ
gfs	V <sub>GS</sub> =5V, I <sub>D</sub> =5A	-	33	-	S
Ciss	Vps=15V Vcs=0V		255		pF
coss	f=1.0MHz		45		
CRSS	_		35		
tD(ON)		-	4.5	-	ns
tr	V <sub>DS</sub> =15V V <sub>GS</sub> =10V	-	2.5	-	
tD(OFF)	R <sub>L</sub> =2.6 ohm R <sub>GEN</sub> =3ohm	-	14.5	-	
tf		-	3.5	-	
Qg		-	5.2	-	
Qgs	V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A	-	0.85	-	nC
Qgd	VGS=1UV	-	1.3	-	
V <sub>SD</sub>	V <sub>GS</sub> =0V,Is=1A	-	0.76	1.16	V
	BV <sub>DSS</sub> IDSS  IGSS  VGS(th)  RDS(ON)  gfs  Ciss  COSS  CRSS  tD(ON)  tr  tD(OFF)  tf  Qg  Qgs  Qgd	BV <sub>DSS</sub>   V <sub>GS</sub> =0V, I <sub>D</sub> =250μA     IDSS   V <sub>DS</sub> =30V, V <sub>GS</sub> =0V     IGSS   V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V     VGS(th)   V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA     V <sub>GS</sub> =10V, I <sub>D</sub> =5A     V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A     V <sub>GS</sub> =5V, I <sub>D</sub> =5A     C <sub>ISS</sub>   V <sub>DS</sub> =15V, V <sub>GS</sub> =0V     CCSS   tD(ON)     tr   V <sub>DS</sub> =15V V <sub>GS</sub> =10V     R <sub>L</sub> =2.6 ohm     R <sub>GEN</sub> =3ohm     tf   Qg     Qgs   V <sub>DS</sub> =15V, I <sub>D</sub> =5.8A     V <sub>GS</sub> =10V     Qgd   V <sub>DS</sub> =10V     Qgd   Qgd   Qgd   Qgd   Qgd     Qgd   Qgd   Qgd   Qgd   Qgd   Qgd     Qgd   Qgd   Qgd   Qgd   Qgd   Qgd     Qgd	BV <sub>DSS</sub> V <sub>GS</sub> =0V, I <sub>D</sub> =250μA 30  IDSS V <sub>DS</sub> =30V, V <sub>GS</sub> =0V -  IGSS V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V -  VGS(th) V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA 0.8  RDS(ON) V <sub>GS</sub> =10V, I <sub>D</sub> =5A -  V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A -  C <sub>ISS</sub> V <sub>DS</sub> =15V,V <sub>GS</sub> =0V f=1.0MHz  CRSS tD(ON) -  tr V <sub>DS</sub> =15V V <sub>GS</sub> =10V R <sub>E</sub> =2.6 ohm R <sub>GEN</sub> =3ohm -  Qg -  Qgs V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A -  Qgd -  Qgd -  Qgd -  Qgd -  Qgd -  Qgd -  COSS -	BV <sub>DSS</sub> V <sub>GS</sub> =0V, I <sub>D</sub> =250μA 30 -  IDSS V <sub>DS</sub> =30V, V <sub>GS</sub> =0V  IGSS V <sub>DS</sub> =0V, V <sub>GS</sub> =±20V  VGS(th) V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250μA 0.8 1.4  V <sub>GS</sub> =10V, I <sub>D</sub> =5A - 24  RDS(ON) V <sub>DS</sub> =4.5V, I <sub>D</sub> =4A 26  gfs V <sub>GS</sub> =5V, I <sub>D</sub> =5A - 33  Clss V <sub>DS</sub> =15V, V <sub>GS</sub> =0V f=1.0MHz 45  CRSS 35  tD(ON) - 4.5  tr V <sub>DS</sub> =15V V <sub>GS</sub> =10V R <sub>L</sub> =2.6 ohm R <sub>GEN</sub> =3ohm - 14.5  Qg - 5.2  Qgg V <sub>DS</sub> =15V,I <sub>D</sub> =5.8A V <sub>GS</sub> =10V - 0.85  Qgd - 5.2  Qgd - 1.3	BVDSS VGS=0V, ID=250μA 30 1 IDSS VDS=30V, VGS=0V 1 IGSS VDS=0V, VGS=±20V ±100 VGS(th) VDS=VGS, ID=250μA 0.8 1.4 2.2  VGS=10V, ID=5A - 24 28  VGS=4.5V, ID=4A 26 32  GfS VGS=5V, ID=5A - 33 255  CISS VDS=15V, VGS=0V f=1.0MHz 45  CRSS

#### Notes:

- 1、surface mounted on FR4 board,t≤10sec
- 2、pulse test: pulse width≤300µs,duty≤2%
- $\ensuremath{\mathtt{3}}_{\times}$  guaranteed by design, not subject to production testing



### **Typical Performance Characteristics**

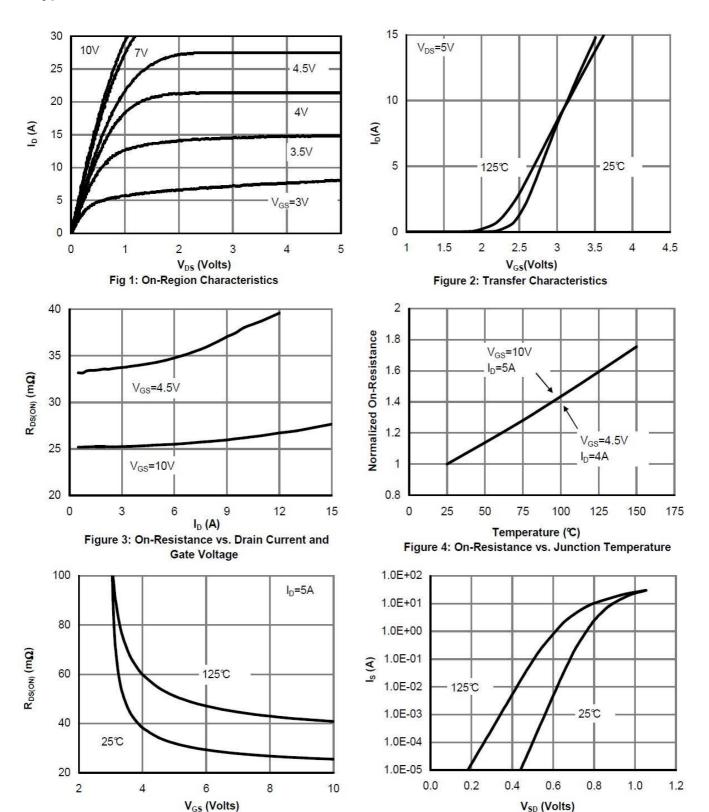
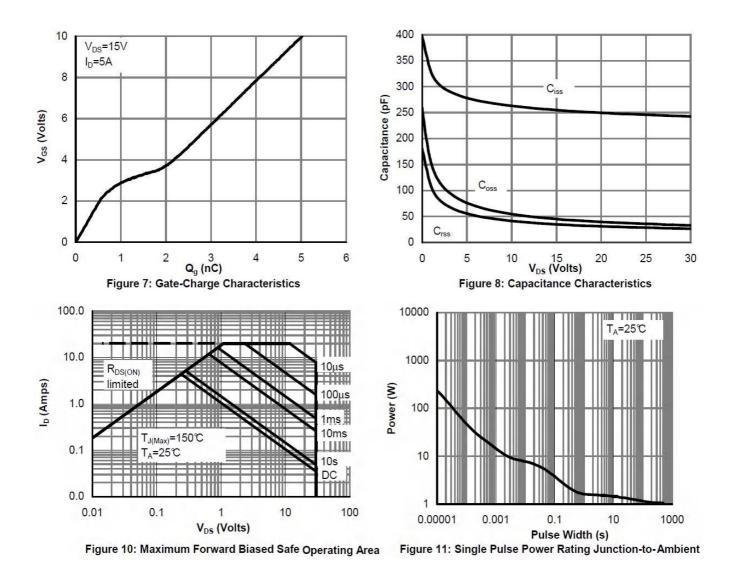


Figure 5: On-Resistance vs. Gate-Source Voltage

Figure 6: Body-Diode Characteristics

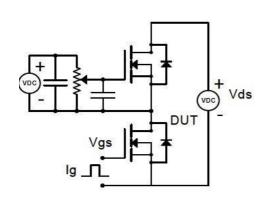


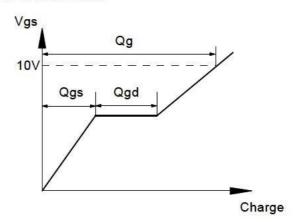
10 In descending order Z<sub>eJA</sub> Normalized Transient D=0.5, 0.3, 0.1, 0.05, 0.02, 0.01, single pulse  $K=T_A+P_{DM}.Z_{\theta JA}.R_{\theta JA}$ Thermal Resistance =125℃/W 0.1 Pn 0.01 Single Pulse  $T_{on}$ 0.001 0.00001 0.0001 0.001 0.01 0.1 1000 10 100 1 Pulse Width (s)

Figure 12: Normalized Maximum Transient Thermal Impedance



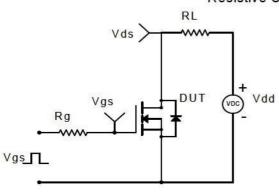
## Gate Charge Test Circuit & Waveform

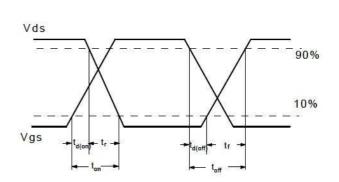




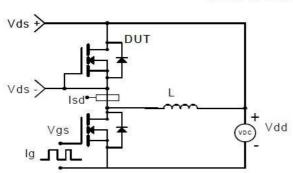
### Resistive Switching Test Circuit & Waveforms

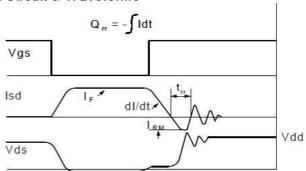
### Resistive Switching Test Circuit & Waveforms



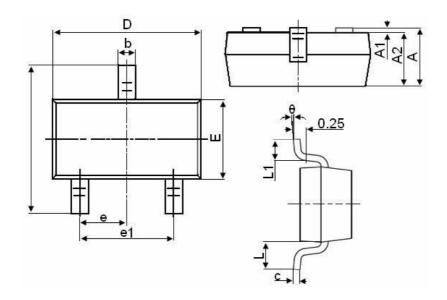


### Diode Recovery Test Circuit & Waveforms





## **SOT-23-3LPackage Information**



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



#### **Attention**

- Any and all HUA XUAN YANG ELECTRONICS products described or contained herein do not have specifications that can handle applications that require extremely high levels of reliability, such as life-support systems, aircraft's control systems, or other applications whose failure can be reasonably expected to result in serious physical and/or material damage. Consult with your HUA XUAN YANG ELECTRONICS representative nearest you before using any HUA XUAN YANG ELECTRONICS products described or contained herein in such applications.
- HUA XUAN YANG ELECTRONICS assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein.
- Specifications of any and all HUA XUAN YANG ELECTRONICS products described or contained herein stipulate the performance, characteristics, and functions of the described products in the independent state, and are not guarantees of the performance, characteristics, and functions of the described products as mounted in the customer's products or equipment. To verify symptoms and states that cannot be evaluated in an independent device, the customer should always evaluate and test devices mounted in the customer's products or equipment.
- HUA XUAN YANG ELECTRONICS CO.,LTD. strives to supply high-quality high-reliability products. However, any and all semiconductor products fail with some probability. It is possible that these probabilistic failures could give rise to accidents or events that could endanger human lives, that could give rise to smoke or fire, or that could cause damage to other property. When designing equipment, adopt safety measures so that these kinds of accidents or events cannot occur. Such measures include but are not limited to protective circuits and error prevention circuits for safe design, redundant design, and structural design.
- In the event that any or all HUA XUAN YANG ELECTRONICS products(including technical data, services) described or contained herein are controlled under any of applicable local export control laws and regulations, such products must not be exported without obtaining the export license from the authorities concerned in accordance with the above law.
- No part of this publication may be reproduced or transmitted in any form or by any means, electronic or mechanical, including photocopying and recording, or any information storage or retrieval system, or otherwise, without the prior written permission of HUA XUAN YANG ELECTRONICS CO.,LTD.
- Information (including circuit diagrams and circuit parameters) herein is for example only; it is not guaranteed for volume production.

  HUA XUAN YANG ELECTRONICS believes information herein is accurate and reliable, but no guarantees are made or implied regarding its use or any infringements of intellectual property rights or other rights of third parties.
- Any and all information described or contained herein are subject to change without notice due to product/technology improvement, etc. When designing equipment, refer to the "Delivery Specification" for the HUA XUAN YANG ELECTRONICS product that you intend to use.